

NPN/PNP Silicon Digital Transistor Array

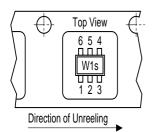
- Switching circuit, inverter, interface circuit, driver circuit
- Two (galvanic) internal isolated NPN/PNP Transistors in one package
- Built in bias resistor NPN and PNP $(R_1=22 \text{ k}\Omega, R_2=22 \text{ k}\Omega)$
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101







Tape loading orientation



Marking on SOT-363 package (for example W1s) corresponds to pin 1 of device

Position in tape: pin 1 opposite of feed hole side

Туре	Marking	Pin Configuration					Package	
BCR22PN	WPs	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT363

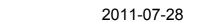
Maximum Ratings for NPN and PNP Types

Symbol	Value	Unit	
V _{CEO}	50	V	
V_{CBO}	50		
V _{i(fwd)}	60		
V _{i(rev)}	10		
I _C	100	mA	
P _{tot}	250	mW	
$T_{\rm j}$	150	°C	
T _{sta}	-65 150		
·	$V_{\rm CEO}$ $V_{\rm CBO}$ $V_{\rm i(fwd)}$ $V_{\rm i(rev)}$ $I_{\rm C}$ $P_{\rm tot}$ $T_{\rm j}$	VCEO 50 VCBO 50 Vi(fwd) 60 Vi(rev) 10 IC 100 Ptot 250 Tj 150	

R_{thJS} K/W Junction - soldering point¹⁾ ≤ 140

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 $^{^{1}}$ For calculation of $R_{
m thJA}$ please refer to Application Note AN077 (Thermal Resistance Calculation)





Electrical Characteristics at T_A =25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics for NPN and PNP Types	•			•	
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	50	-	-	V
$I_{\rm C}$ = 100 μ A, $I_{\rm B}$ = 0					
Collector-base breakdown voltage	V _{(BR)CBO}	50	-	-	
$I_{\rm C}$ = 10 μ A, $I_{\rm E}$ = 0	, ,				
Collector cutoff current	I _{CBO}	-	-	100	nA
$V_{\text{CB}} = 40 \text{ V}, I_{\text{E}} = 0$					
Emitter cutoff current	I _{EBO}	-	-	350	μΑ
$V_{\rm EB}$ = 10 V, $I_{\rm C}$ = 0					
DC current gain 1)	h _{FE}	50	-	-	-
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 5 V					
Collector-emitter saturation voltage1)	V _{CEsat}	-	-	0.3	V
$I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 0.5 mA					
Input off voltage	$V_{i(off)}$	8.0	-	1.5	
$I_{\rm C}$ = 100 μ A, $V_{\rm CE}$ = 5 V					
Input on Voltage	V _{i(on)}	1	-	2.5	
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 0.3 V					
Input resistor	R ₁	15	22	29	kΩ
Resistor ratio	R_1/R_2	0.9	1	1.1	-
AC Characteristics for NPN and PNP Types					
Transition frequency	f _T	-	130	-	MHz
$I_{\rm C}$ = 10 mA, $V_{\rm CE}$ = 5 V, f = 100 MHz					
Collector-base capacitance	C _{cb}	-	3	-	pF
$V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$					

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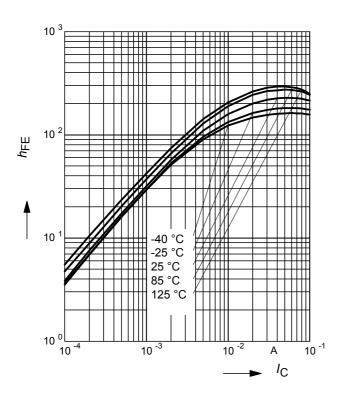
¹⁾ Pulse test: $t < 300\mu s$; D < 2%



NPN Type

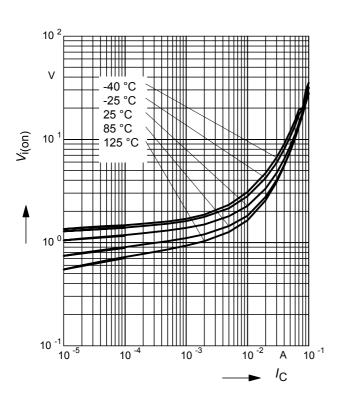
DC Current Gain $h_{FE} = f(I_C)$

 V_{CF} = 5V (common emitter configuration)



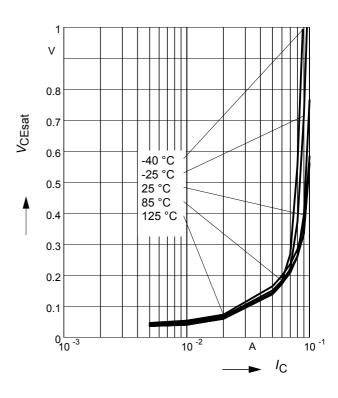
Input on Voltage $V_{i(On)} = f(I_C)$

 V_{CE} = 0.3V (common emitter configuration)



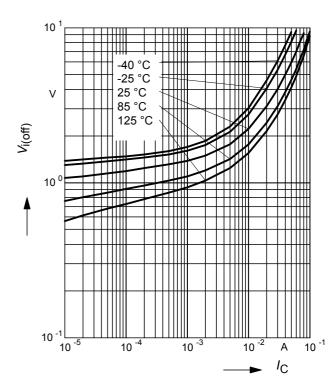
Collector-Emitter Saturation Voltage

 $V_{\text{CEsat}} = f(I_{\text{C}}), h_{\text{FE}} = 20$



Input off voltage $V_{i(Off)} = f(I_C)$

 V_{CE} = 5V (common emitter configuration)

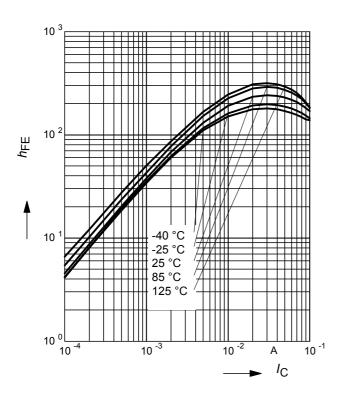




PNP Type

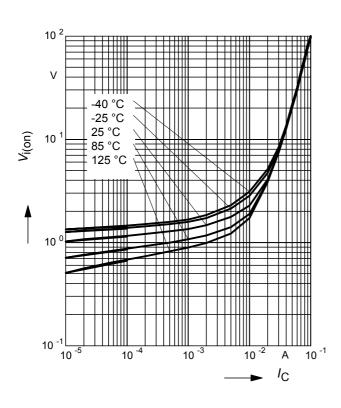
DC Current Gain $h_{FE} = f(I_C)$

 V_{CF} = 5V (common emitter configuration)



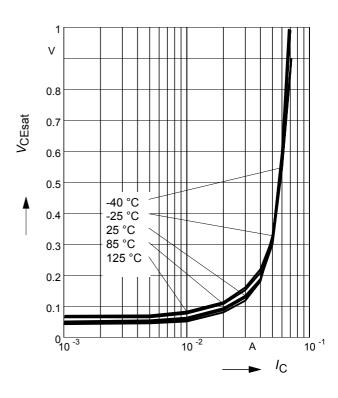
Input on Voltage $V_{i(On)} = f(I_C)$

 V_{CE} = 0.3V (common emitter configuration)



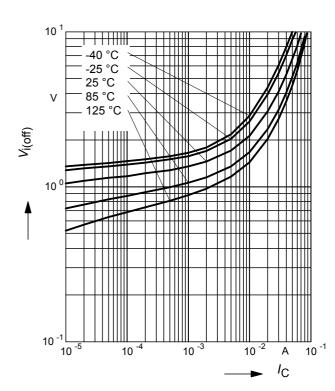
Collector-Emitter Saturation Voltage

 $V_{\text{CEsat}} = f(I_{\text{C}}), h_{\text{FE}} = 20$



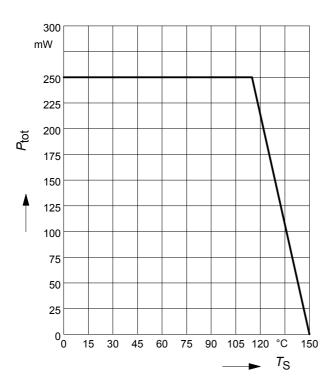
Input off voltage $V_{i(Off)} = f(I_C)$

 V_{CE} = 5V (common emitter configuration)





Total power dissipation $P_{tot} = f(T_S)$

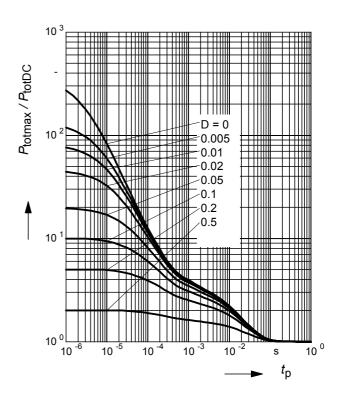


Permissible Pulse Load $R_{thJS} = f(t_p)$

10 ³ 10 ¹ 10 ¹

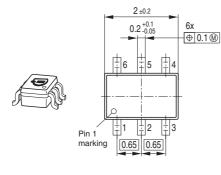
Permissible Pulse Load

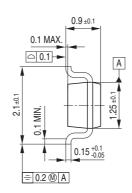
$$P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$$



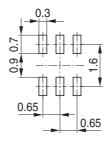


Package Outline



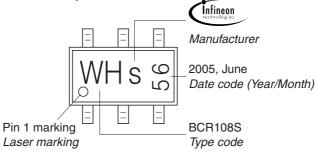


Foot Print



Marking Layout (Example)

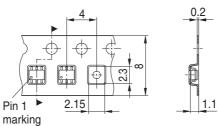
Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



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Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

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